

2MBI225XNB120-50

IGBT Modules

Power Module (X series) 1200V / 225A / 2-in-1 package

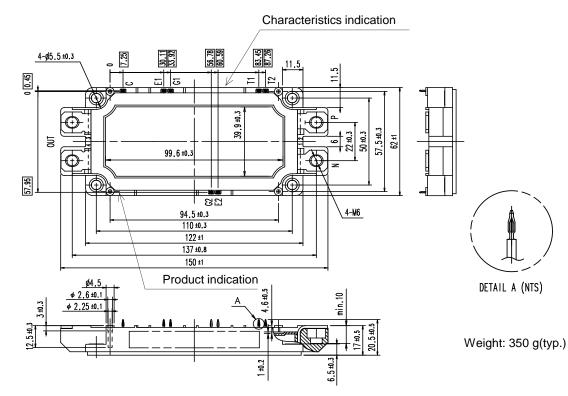
Features

Low $V_{CE(sat)}$ Low Inductance Module structure Press fit pin terminals

Applications

Inverter for Motor Drives, AC and DC Servo Drives Uninterruptible Power Supply Systems, Wind Turbines, PV Power Conditioning Systems

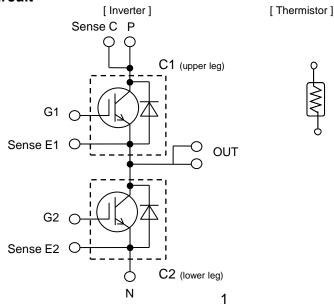
■ Outline drawing (Unit : mm)



Τ1

T2

NOTE) _____ shows theoretical dimension and tolerance is \$_\$\\$0.5}
Equivalent Circuit





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■ Absolute Maximum Ratings (at T_c= 25°C unless otherwise specified)

Items			Symbols	Cond	litions	Maximum Ratings	Units
	Collecto	r-emitter voltage, gate-emitter short-circuited	V _{CES}			1200	V
	Gate-en	nitter voltage, collector-emitter short-circuited	V _{GES}			±20	V
	Collecto	r current	I _C	Continuous	$T_{\rm C}=100^{\circ}{\rm C}$	225	
	Repetitiv	e peak collector current	I _{CRM}	1ms	1	450	_
rter	Forward	current	/ _F			225	A
Forward current Repetitive peak forward current			/ _{FRM}	1ms		450	1
Total power dissipation		P _{tot}	1 device		1030	W	
Virtual junction temperature			T_{vj}			175	
	Operating junction temperature					175	°C
(under switching conditions)			${\cal T}_{ m vjop}$				
Са	Case temperature		T _c			125	1
Storage temperature		T _{stg}			-40 ~ 125		
Isolation between terminal and copper base (*1)		V	AC: 1min.		2500	Vrms	
voltage between thermistor and others (*2)		V _{isol}	AC. Imin.		2500	vinis	
Mo	Mounting torque of screws to heatsink (*3)		Ms	M5		6.0	N⋅m
Мс	ounting to	rque of screws to terminals (*3)	M _t	M6		6.0	

(*1) All terminals should be connected together during the test.

(*2) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*3)Recommendable Value:: Mounting torque of screws to heatsink $2.5 \sim 6.0 \text{ N·m}$ (M5)Recommendable Value:: Mounting torque of screws to terminals $3.5 \sim 6.0 \text{ N·m}$ (M6)



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■ Electrical characteristics (at *T*_{vj}= 25°C unless otherwise specified)

	Items	Symbols		Conditio	ne	Characteristics			Unite
	items	Sindors		Conditions			typ. max.		Units
	Collector-emitter cut-off current, gate-emitter short- circuited	I _{CES}	V _{GE} = V _{CE} =	0V 1200V		-	-	150	μA
	Gate leakage current, collector-emitter short- circuited	I _{GES}	V _{CE} =0V	∕, V _{GE} =±20)V	-	-	300	nA
	Gate-Emitter threshold voltage	$V_{\rm GE(th)}$	V _{CE} = I _C =	20V 225mA		6.0	6.5	7.0	V
		V _{CE(sat)} (terminal)			T _{vj} =25°C	-	1.75	2.20	
	Collector-Emitter		V _{GE} = 1	5V	T _{vj} =25°C	-	1.45	1.90	
	saturation voltage	V _{CE(sat)}	/ _C =		T _{vi} =125°C	-	1.80	-	- V
		(chip)			T _{vi} =150°C	-	1.90	-	-
					, <i>T</i> _{νj} =175°C	-	1.95	-	
	Internal gate resistance	r _g	-		· vj · · · · ·	-	5.00	-	Ω
		C _{ies}				-	24	-	
	Capacitance	C _{oes}	V _{CE} =10V, V _{GE} =0V, f=1MHz			-	0.8	-	nF
		C _{res}				-	0.21	-	
	Gate charge	Q _G		600V, $I_{\rm C}$ -15 → +1		-	1.6	-	μC
Inverter		V _F (terminal)	$V_{GE} = 0$ $I_F = 225$	V	T _{vj} =25°C	-	1.90	2.35	
IVel					T _{vj} =25°C	-	1.60	2.05	_
<u>_</u>	Forward voltage	V _F			, T _{vj} =125°C	-	1.65	-	- V
		(chip)			$T_{\rm vi}$ =150°C	-	1.60	-	_
					$T_{vj}=175^{\circ}C$	-	1.60	-	-
			V _{CC} =	600\/	$T_{vj}=170^{\circ}C$ $T_{vj}=25^{\circ}C$	-	0.23	-	
			$I_{\rm C}, I_{\rm F} =$		$T_{vj}=125^{\circ}C$	-	0.20	-	_
		t _{d(on)}	-			-	0.27	-	_
			-	-)	0.28	-	-		
		t _r	-	35 nH	$T_{vj}=25^{\circ}C$	-	0.07	-	_
			-5		<i>T</i> _{vi} =125°C	-	0.08	-	_
					_{vj} =150°C	-	0.08	-	-
	Switching time (*1)				τ _{vi} =175°C	-	0.08	-	-
	Switching time (1)		-		$T_{\rm vi}=25^{\circ}\rm C$	-	0.33	-	-
		4			7 _{vi} =125°C	-	0.35	-	μs
		$t_{d(off)}$			τ _{vi} =150°C	-	0.35	-	1
					T _{vj} =175°C	-	0.36	-]
					$T_{\rm vj}=25^{\circ}\rm C$	-	0.05	-	4
		t _f			$T_{vj} = 125^{\circ}C$	-	0.06	-	4
					$T_{vj} = 150^{\circ}C$	-	0.07	-	4
			-		<i>T</i> _{vj} =175°C <i>T</i> _{vi} =25°C	-	0.08 0.14	-	-
					$T_{vj} = 125^{\circ}C$		0.14	-	-
	Reverse recovery time	t _{rr}			$T_{vj} = 150^{\circ}C$	-	0.35	-	1
			1		T _{vi} =175°C	-	0.40	-	-

(*1) Turn on time $(t_{on}) = t_{d(on)} + t_r$, Turn off time $(t_{off}) = t_{d(off)} + t_f$



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Items		Symbols	Conditions			Characteristics			Units
	Items	Symbols	Conditions			min.	typ.	max.	Units
			$V_{\rm CC} =$		T _{vj} =25°C	-	21.5	-	
	Switching loss	E _{on}	1 _C , 1 _F	= 225A	T _{vj} =125°C T _{vj} =150°C	-	31.4	-	
			$V_{\rm GE} =$	+15/-15 V	T _{vj} =150°C	-	35.1	-	
			$R_{\rm G} =$	±0.82Ω	T _{vj} =175°C	-	38.6	-	
			$L_{\rm S} =$	35 nH	T _{vj} =25°C	-	14.3	-	
ē					T _{vj} =125°C	-	17.9	-	
Inverter	(per pulse)	E _{off}			T _{vj} =150°C	_{vj} =150°C - 18.8	-	mJ	
Ē	(PC: PC:C)				T _{vj} =175°C	-	20.6	-	
			1		T _{vj} =25°C	-	9.1	-	1
		Err			T _{vj} =125°C	-	14.0	-	
		L rr	<i>L</i> _{rr} <i>T</i> _{vj} =150°C -	15.7	-				
					<i>T</i> _{vj} =175°С	-	18.7	-	
tor	Resistance	R	<i>T</i> =	25°C		-	5000	-	Ω
nis			<i>T</i> =	100°C		465	495	520	
Thermistor	B value	В	<i>T</i> =	25/ 50°C		3305	3375	3450	К

■ Electrical characteristics (at T_{vj}= 25°C unless otherwise specified)

NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

Thermal resistance characteristics

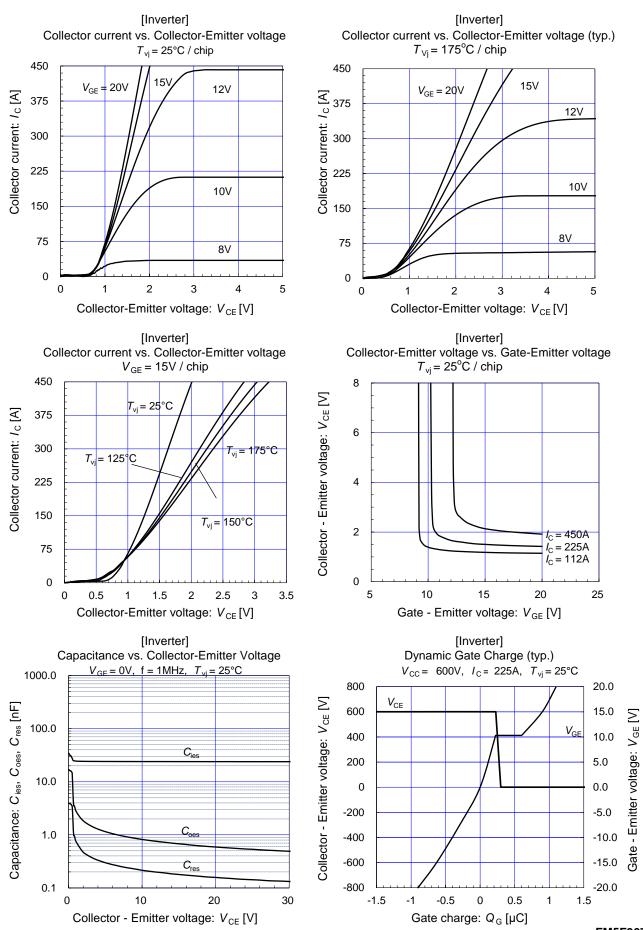
Items	Symbols	Conditions	Ch	Characteristics			
items	Symbols Conditions		min.	typ.	max.	Units	
Thermal resistance junction to	P	Inverter IGBT	-	-	0.145		
case(1 device)	$R_{\mathrm{th(j-c)}}$	Inverter FWD	-	-	0.190	к/w	
Thermal resistance case to	$R_{\rm th(c-s)}$	with 1 W/(m·K) thermal grease	-	0.0167	_	1	
heatsink(1 IGBT+1 FWD) (*1)	T th(c-s)	with T W/(III-R) thermal grease	-	0.0107	-		

(*1) This is the value which is defined mounting on the additional heatsink with thermal grease.



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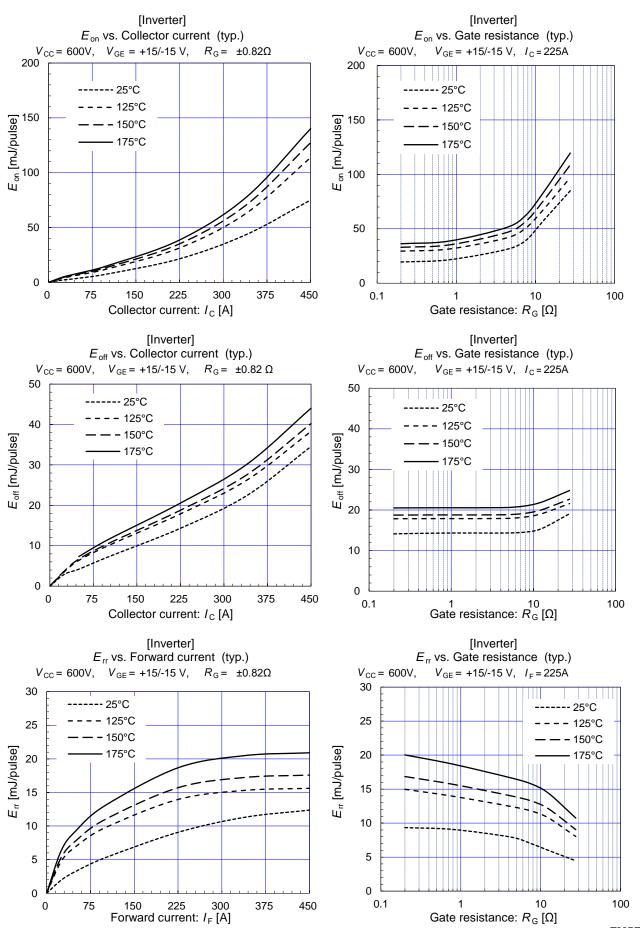


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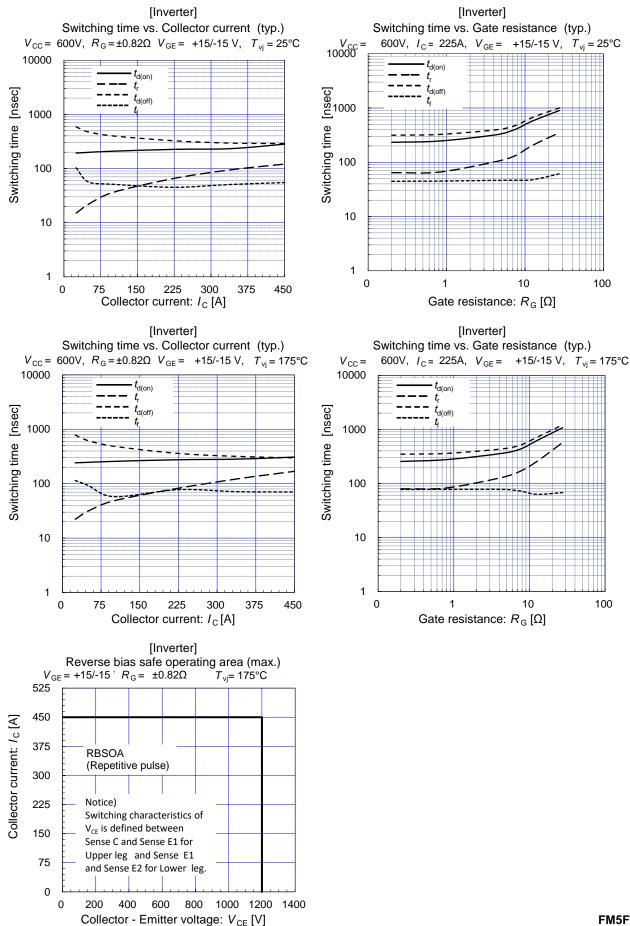
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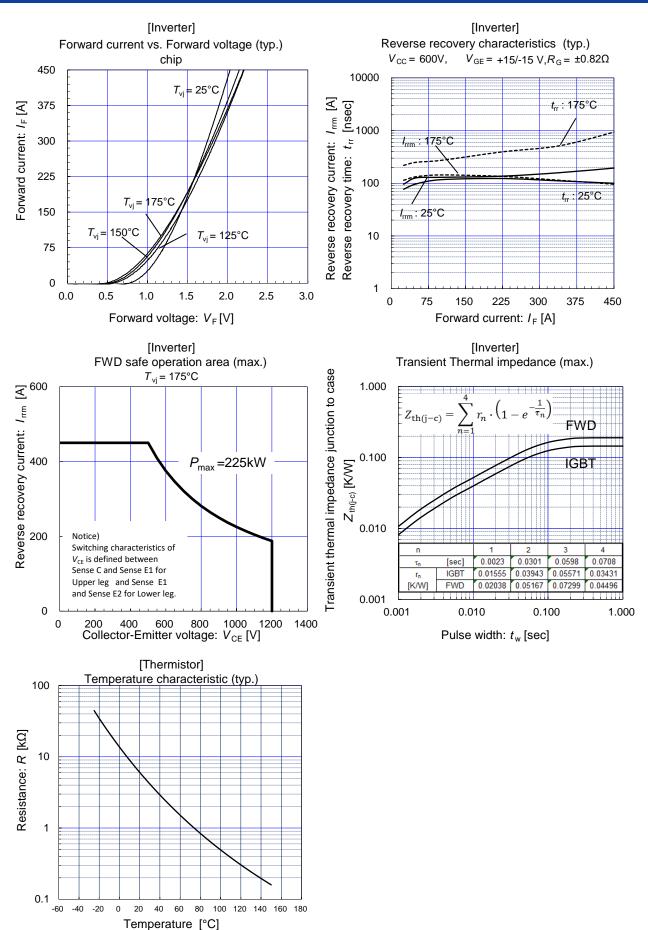


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